MJB44H11 (NPN), NJVMJB44H11 (NPN), MJB45H11 (PNP), NJVMJB45H11 (PNP)

Complementary Power Transistors

D²PAK for Surface Mount

Complementary power transistors are for general purpose power amplification and switching such as output or driver stages in applications such as switching regulators, converters and power amplifiers.

Features

- Low Collector–Emitter Saturation Voltage –
 V_{CE(sat)} = 1.0 V (Max) @ 8.0 A
- Fast Switching Speeds
- Complementary Pairs Simplifies Designs
- Epoxy Meets UL 94 V-0 @ 0.125 in
- ESD Ratings: Human Body Model, 3B > 8000 V Machine Model, C > 400 V
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- Pb-Free Packages are Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	80	Vdc
Emitter-Base Voltage	V _{EB}	5	Vdc
Collector Current – Continuous – Peak	I _C	10 20	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	50 0.4	W W/°C
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	2.0 0.016	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to 150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.5	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	75	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1



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SILICON POWER TRANSISTORS 10 AMPERES, 80 VOLTS, 50 WATTS

MARKING DIAGRAM



D²PAK CASE 418B STYLE 1



c = 4 or 5

= Assembly Location

= Year

/W = Work Week

= Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
MJB44H11G	D ² PAK (Pb-Free)	50 Units/Rail
MJB44H11T4G	D ² PAK (Pb-Free)	800/Tape & Reel
NJVMJB44H11T4G	D ² PAK (Pb-Free)	800/Tape & Reel
MJB45H11G	D ² PAK (Pb-Free)	50 Units/Rail
MJB45H11T4G	D ² PAK (Pb-Free)	800/Tape & Reel
NJVMJB45H11T4G	D ² PAK (Pb-Free)	800/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MJB44H11 (NPN), NJVMJB44H11 (NPN), MJB45H11 (PNP), NJVMJB45H11 (PNP)

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Collector-Emitter Sustaining Voltage (I _C = 30 mA, I _B = 0)	V _{CEO(sus)}	80	-	-	Vdc	
Collector Cutoff Current (V _{CE} = Rated V _{CEO} , V _{BE} = 0)	I _{CES}	-	-	10	μΑ	
Emitter Cutoff Current (V _{EB} = 5 Vdc)	I _{EBO}	-	-	50	μΑ	
ON CHARACTERISTICS						
Collector-Emitter Saturation Voltage (I _C = 8 Adc, I _B = 0.4 Adc)	V _{CE(sat)}	-	-	1.0	Vdc	
Base-Emitter Saturation Voltage (I _C = 8 Adc, I _B = 0.8 Adc)	V _{BE(sat)}	-	-	1.5	Vdc	
DC Current Gain (V _{CE} = 1 Vdc, I _C = 2 Adc)	h _{FE}	60	-	-	-	
DC Current Gain (V _{CE} = 1 Vdc, I _C = 4 Adc)		40	-	-		
DYNAMIC CHARACTERISTICS						
Collector Capacitance (V _{CB} = 10 Vdc, f _{test} = 1 MHz) MJB44H11, NJVMJB44H1 MJB45H11, NJVMJB45H1		_ _	130 230	_ _	pF	
Gain Bandwidth Product (I _C = 0.5 Adc, V _{CE} = 10 Vdc, f = 20 MHz) MJB44H11, NJVMJB44H1 MJB45H11, NJVMJB45H1		- -	50 40	- -	MHz	
SWITCHING TIMES						
Delay and Rise Times(I _C = 5 Adc, I _{B1} = 0.5 Adc) MJB44H11, NJVMJB44H1 MJB45H11, NJVMJB45H1		- -	300 135	- -	ns	
Storage Time(I _C = 5 Adc, I _{B1} = I _{B2} = 0.5 Adc) MJB44H11, NJVMJB44H1 MJB45H11, NJVMJB45H1		-	500 500	- -	ns	
Fall Time(I _C = 5 Adc, I _{B1} = I _{B2} = 0.5 Adc) MJB44H11, NJVMJB44H1 MJB45H11, NJVMJB45H11		- -	140 100	- -	ns	

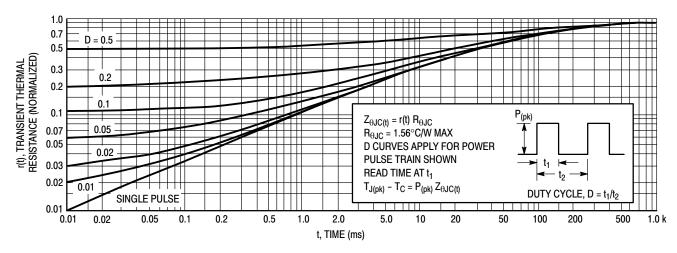


Figure 1. Thermal Response

MJB44H11 (NPN), NJVMJB44H11 (NPN), MJB45H11 (PNP), NJVMJB45H11 (PNP)

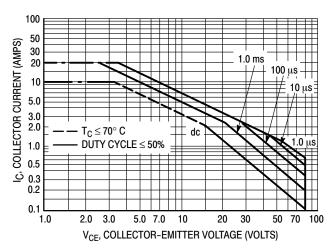


Figure 2. Maximum Rated Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on $T_{J(pk)} = 150^{\circ}\text{C}$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ}\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 1. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

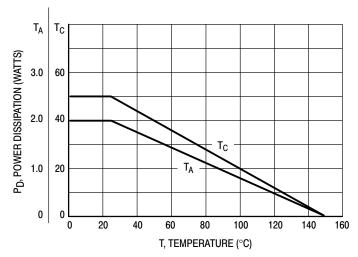


Figure 3. Power Derating

MJB44H11 (NPN), NJVMJB44H11 (NPN), MJB45H11 (PNP), NJVMJB45H11 (PNP)

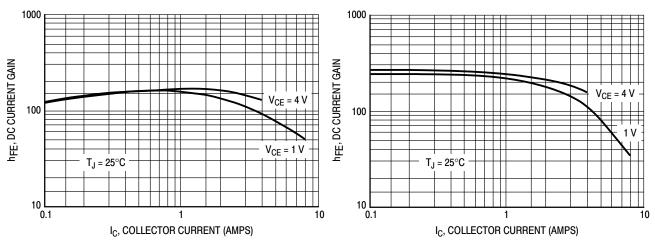


Figure 4. MJB44H11 DC Current Gain

Figure 5. MJB45H11 DC Current Gain

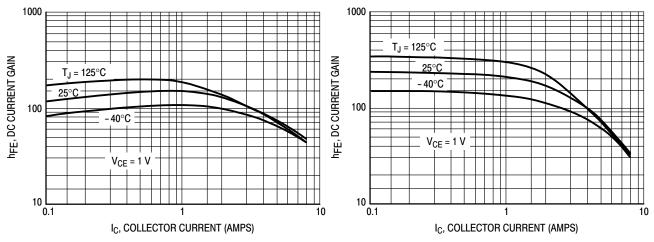


Figure 6. MJB44H11 Current Gain versus Temperature

Figure 7. MJB45H11 Current Gain versus Temperature

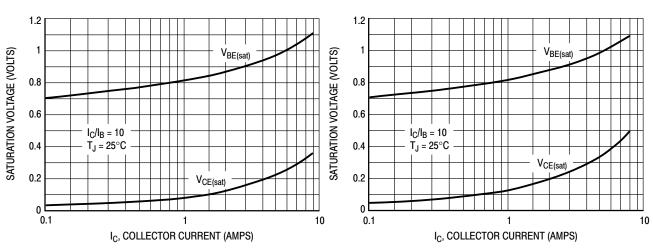


Figure 8. MJB44H11 On-Voltages

Figure 9. MJB45H11 On-Voltages

MECHANICAL CASE OUTLINE

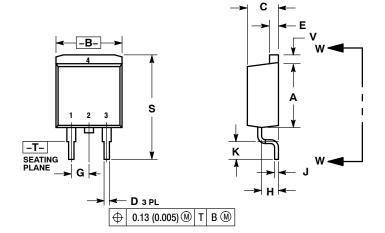




D²PAK 3 CASE 418B-04 **ISSUE L**

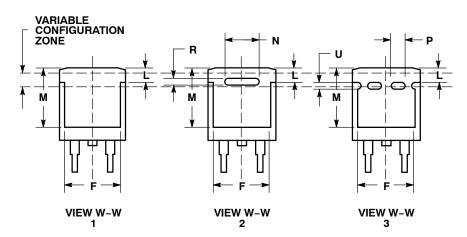
DATE 17 FEB 2015

SCALE 1:1



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
- 3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

	INCHES		MILLIMETER	
DIM	MIN	MAX	MIN	MAX
Α	0.340	0.380	8.64	9.65
В	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
Е	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
Н	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
М	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
Р	0.079 REF		2.00 REF	
R	0.039	REF	0.99 REF	
S	0.575	0.625	14.60	15.88
٧	0.045	0.055	1.14	1.40



STYLE 1: PIN 1. BASE 2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN STYLE 3:

PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE

STYLE 4:

PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 5:

PIN 1. CATHODE 2. ANODE 3. CATHODE 4. ANODE

STYLE 6:

PIN 1. NO CONNECT
2. CATHODE
3. ANODE
4. CATHODE

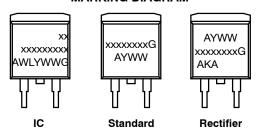
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GENERIC MARKING DIAGRAM*



xx = Specific Device Code A = Assembly Location

 WL
 = Wafer Lot

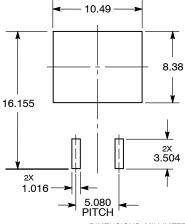
 Y
 = Year

 WW
 = Work Week

 G
 = Pb-Free Package

 AKA
 = Polarity Indicator

SOLDERING FOOTPRINT*



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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot " ■", may or may not be present.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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